

英飞凌IMZA120R078M2H

CoolSiC™ 1200 V SiC MOSFET G2

CoolSiC™ 1200 V SiC MOSFET G2：采用.XT 互连技术的碳化硅 MOSFET

特性

- $T_{vj} = 25^{\circ}\text{C}$ 时 $V_{DSS} = 1200\text{ V}$
- $I_{DDC} = 20\text{ A}$ at $T_C = 100^{\circ}\text{C}$
- $R_{DS(on)} = 78\text{ m}\Omega$ at $V_{GS} = 18\text{ V}$, $T_{vj} = 25^{\circ}\text{C}$
- 开关损耗非常低
- 过载运行最高结温可达 $T_{vj} = 200^{\circ}\text{C}$
- 短路耐受时间 $2\text{ }\mu\text{s}$
- 基准栅极阈值电压, $V_{GS(th)} = 4.2\text{ V}$
- 具有抗寄生导通能力, 可应用 0 V 关断栅极电压
- 坚固的体二极管, 适用于硬换向
- .XT 互连技术, 实现、行业领先的热性能
- 合适的英飞凌栅极驱动器可在 <https://www.infineon.com/gdfinder> 找到

潜在应用

- 通用驱动器 (GPD)
- 电动汽车充电桩
- 在线式UPS/工业UPS
- 组串式逆变器
- 储能系统(ESS)
- 焊接

产品验证

- 符合JEDEC47/20/22相关测试的工业应用要求

描述

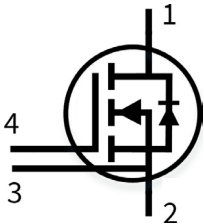
引脚定义：

- 引脚 1 – 漏极
- 引脚 2 – 源
- 引脚 3 – 开尔文检测触点
- 引脚 4 – 栅极

注：源极引脚和检测引脚不可互换，互换可能会导致故障



- Halogen-free
- Green
- Lead-free
- RoHS



Type	Package	Marking
IMZA120R078M2H	PG-TO247-4-U02	12M2H078

本数据手册的原文使用英文撰写。为方便起见，英飞凌提供了译文；由于翻译过程中可能使用了自动化工具，英飞凌不保证译文的准确性。为确认准确性，请务必访问 [infineon.com](https://www.infineon.com) 参考最新的英文版本（控制文档）。



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1封装

1 封装

表 1 特征值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	Wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	M	M3 screw, Maximum of mounting processes: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				62	K/W
MOSFET/body diode thermal resistance, junction-case	$R_{th(j-c)}$			0.8	1.04	K/W

2 MOSFET

表2 最大额定值

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25\text{ °C}$		1200	V
Continuous DC drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{DDC}	$V_{GS} = 18\text{ V}$	$T_c = 25\text{ °C}$	28	A
			$T_c = 100\text{ °C}$	20	
Peak drain current, t_p limited by $T_{vj(max)}$ ¹⁾	I_{DM}	$V_{GS} = 18\text{ V}$		98.5	A
Gate-source voltage, max. transient voltage	V_{GS}	$t_p \leq 0.5\text{ }\mu\text{s}$, $D < 0.01$		-10...25	V
Gate-source voltage, max. static voltage ²⁾	V_{GS}			-7...23	V
Avalanche energy, single pulse	E_{AS}	$I_D = 9\text{ A}$, $V_{DD} = 50\text{ V}$, $L = 2.8\text{ mH}$, $T_{vj(start)} = 25\text{ °C}$		112	mJ
Avalanche energy, repetitive	E_{AR}	$I_D = 9\text{ A}$, $V_{DD} = 50\text{ V}$, $L = 14.1\text{ }\mu\text{H}$, $T_{vj(start)} = 25\text{ °C}$		0.56	mJ
Short-circuit withstand time	t_{SC}	$V_{DD} \leq 800\text{ V}$, $V_{DS,peak} < 1200\text{ V}$, $V_{GS(on)} = 15\text{ V}$, $T_{vj(start)} = 25\text{ °C}$		2	μs
Power dissipation, limited by $T_{vj(max)}$	P_{tot}		$T_c = 25\text{ °C}$	143	W
			$T_c = 100\text{ °C}$	71	

1) 已通过设计验证。

2) 应用设计中的最大栅源电压应符合IPC-9592B的规定。

表 3 **建议值**

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-on gate voltage	$V_{GS(on)}$		15...18	V
Recommended turn-off gate voltage	$V_{GS(off)}$		-5...0	V

表4 **特征值**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-state resistance	$R_{DS(on)}$	$I_D = 9\text{ A}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$, $V_{GS(on)} = 18\text{ V}$		78	103	mΩ
			$T_{vj} = 150\text{ }^{\circ}\text{C}$, $V_{GS(on)} = 18\text{ V}$		159		
			$T_{vj} = 175\text{ }^{\circ}\text{C}$, $V_{GS(on)} = 18\text{ V}$		185		
			$T_{vj} = 25\text{ }^{\circ}\text{C}$, $V_{GS(on)} = 15\text{ V}$		97	130	
Gate-source threshold voltage	$V_{GS(th)}$	$I_D = 2.8\text{ mA}$, $V_{DS} = V_{GS}$ (tested after 1 ms pulse at $V_{GS} = 20\text{ V}$)	$T_{vj} = 25\text{ }^{\circ}\text{C}$	3.5	4.2	5.1	V
			$T_{vj} = 175\text{ }^{\circ}\text{C}$		3.2		
Zero gate-voltage drain current	I_{DSS}	$V_{DS} = 1200\text{ V}$, $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$			80	μA
			$T_{vj} = 175\text{ }^{\circ}\text{C}$		1		
Gate leakage current	I_{GSS}	$V_{DS} = 0\text{ V}$	$V_{GS} = 23\text{ V}$			120	nA
			$V_{GS} = -10\text{ V}$			-120	
Forward transconductance	g_{fs}	$I_D = 9\text{ A}$, $V_{DS} = 20\text{ V}$			6		S
Internal gate resistance	$R_{G,int}$	$f = 1\text{ MHz}$, $V_{AC} = 25\text{ mV}$			10		Ω
Input capacitance	C_{iss}	$V_{DS} = 800\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$, $V_{AC} = 25\text{ mV}$			700		pF
Output capacitance	C_{oss}	$V_{DS} = 800\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$, $V_{AC} = 25\text{ mV}$			28		pF
Reverse transfer capacitance	C_{rss}	$V_{DS} = 800\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$, $V_{AC} = 25\text{ mV}$			2		pF
C_{oss} stored energy	E_{oss}	Calculated based on $C_{oss} = f(V_{DD})$			12		μJ
Output charge	Q_{oss}	Calculated based on $C_{oss} = f(V_{DD})$			43		nC
Effective output capacitance, energy related	$C_{o(er)}$	$V_{DS} = 0...800\text{ V}$, $V_{GS} = 0\text{ V}$, Calculated based on E_{oss}			38		pF
Effective output capacitance, time related	$C_{o(tr)}$	$I_D = \text{constant}$, $V_{DS} = 0...800\text{ V}$, $V_{GS} = 0\text{ V}$, Calculated based on Q_{oss}			54		pF
Total gate charge	Q_G	$V_{DD} = 800\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = 0/18\text{ V}$, turn-on pulse			21		nC

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表 4 (续) 特征值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Plateau gate charge	$Q_{GS(pl)}$	$V_{DD} = 800\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = 0/18\text{ V}$, turn-on pulse		5		nC
Gate-drain charge	Q_{GD}	$V_{DD} = 800\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = 0/18\text{ V}$, turn-on pulse		5		nC
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 800\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = 0/18\text{ V}$, $R_{G,ext} = 2.3\ \Omega$, $L_\sigma = 12\text{ nH}$, diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	5		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	4.1		
Rise time	t_r	$V_{DD} = 800\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = 0/18\text{ V}$, $R_{G,ext} = 2.3\ \Omega$, $L_\sigma = 12\text{ nH}$, diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	3.2		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	2.8		
Turn-off delay time	$t_{d(off)}$	$V_{DD} = 800\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = 0/18\text{ V}$, $R_{G,ext} = 2.3\ \Omega$, $L_\sigma = 12\text{ nH}$, diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	11.7		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	13.6		
Fall time	t_f	$V_{DD} = 800\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = 0/18\text{ V}$, $R_{G,ext} = 2.3\ \Omega$, $L_\sigma = 12\text{ nH}$, diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	4.8		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	5.6		
Turn-on energy	E_{on}	$V_{DD} = 800\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = 0/18\text{ V}$, $R_{G,ext} = 2.3\ \Omega$, $L_\sigma = 12\text{ nH}$, diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	57		μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$	114		
Turn-off energy	E_{off}	$V_{DD} = 800\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = 0/18\text{ V}$, $R_{G,ext} = 2.3\ \Omega$, $L_\sigma = 12\text{ nH}$, diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	22		μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$	30		
Total switching energy ¹⁾	E_{tot}	$V_{DD} = 800\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = 0/18\text{ V}$, $R_{G,ext} = 2.3\ \Omega$, $L_\sigma = 12\text{ nH}$, diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	110		μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$	233		

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表 4 (续) 特征值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-on energy at -5 V	E_{on}	$V_{DD} = 800\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = -5/18\text{ V}$, $R_{G,ext} = 2.3\ \Omega$, $L_\sigma = 12\text{ nH}$, diode: body diode at $V_{GS} = -5\text{ V}$	$T_{vj} = 25\text{ °C}$	50		μJ
			$T_{vj} = 175\text{ °C}$	109		
Turn-off energy at -5 V	E_{off}	$V_{DD} = 800\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = -5/18\text{ V}$, $R_{G,ext} = 2.3\ \Omega$, $L_\sigma = 12\text{ nH}$, diode: body diode at $V_{GS} = -5\text{ V}$	$T_{vj} = 25\text{ °C}$	12		μJ
			$T_{vj} = 175\text{ °C}$	12		
Total switching energy at -5 V ¹⁾	E_{tot}	$V_{DD} = 800\text{ V}$, $I_D = 9\text{ A}$, $V_{GS} = -5/18\text{ V}$, $R_{G,ext} = 2.3\ \Omega$, $L_\sigma = 12\text{ nH}$, diode: body diode at $V_{GS} = -5\text{ V}$	$T_{vj} = 25\text{ °C}$	93		μJ
			$T_{vj} = 175\text{ °C}$	226		
Virtual junction temperature	T_{vj}		-55		175	$^{\circ}\text{C}$
Virtual junction temperature	$T_{vj(over)}$	overload, cumulative max. 100 h ²⁾			200	$^{\circ}\text{C}$

1) 包括 E_{fr}

2) 最多 5000 次循环。最大 ΔT 限制为 100 K。

注：芯片技术的特征是高达 200 kV/ μs 。测量的 dV/dt 受到测量测试设置和封装的限制。

除非另有规定，特性均为 $T_{vj} = 25^{\circ}\text{C}$ 。

3 体二极管 (MOSFET)

表5 最大额定值

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}	$T_{vj} \geq 25\text{ °C}$		1200	V
Continuous reverse drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$	I_{SDC}	$V_{GS} = 0\text{ V}$	$T_c = 25\text{ °C}$	24	A
			$T_c = 100\text{ °C}$	14	
Peak reverse drain current, t_p limited by $T_{vj(max)}$	I_{SM}	$V_{GS} = 0\text{ V}$		60	A

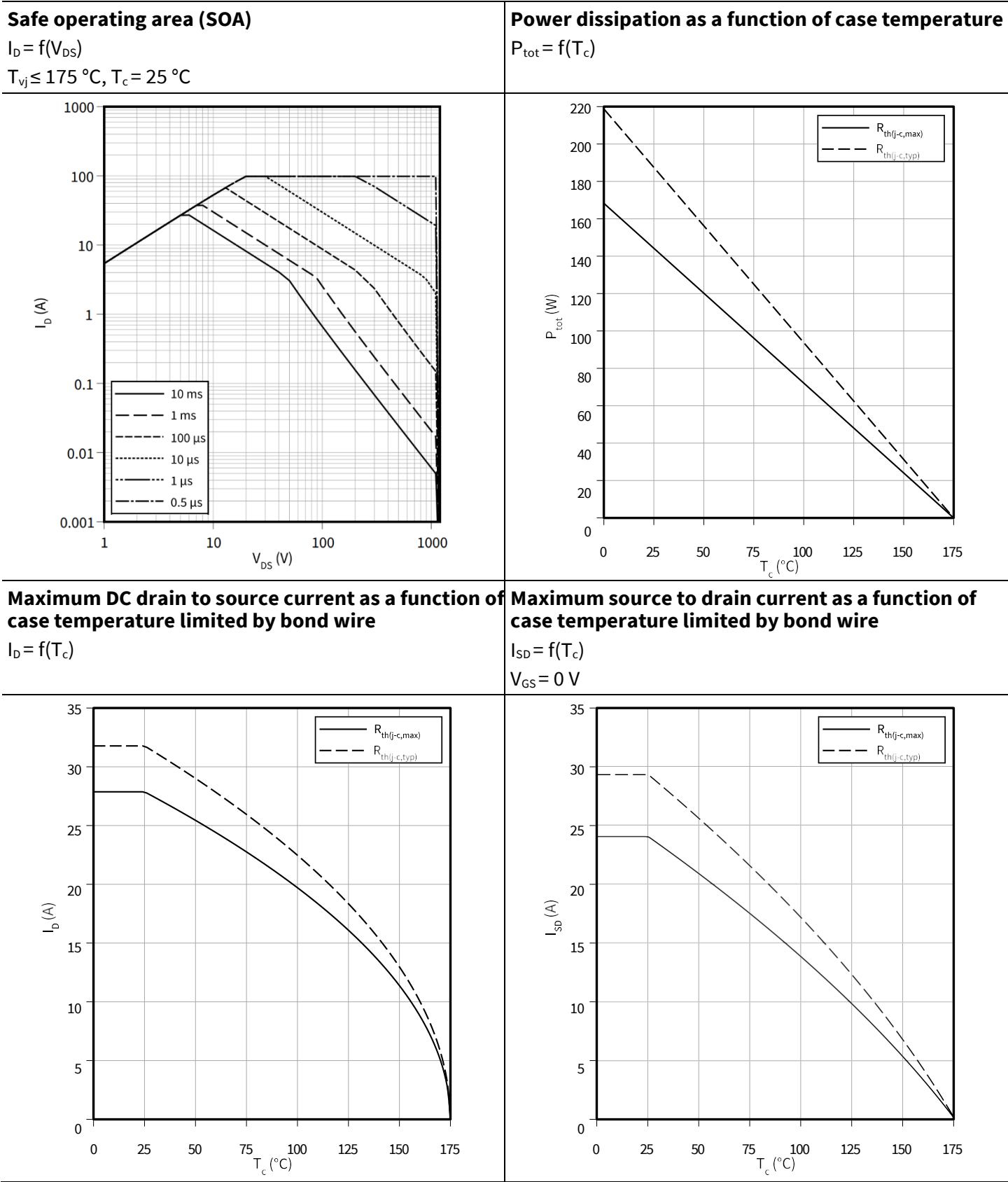
表6 特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source reverse voltage	V_{SD}	$I_{SD} = 9\text{ A}$, $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		4.2	5.5	V
			$T_{vj} = 100\text{ °C}$		4.11		
			$T_{vj} = 175\text{ °C}$		4.05		
MOSFET forward recovery charge	Q_{fr}	$V_{DD} = 800\text{ V}$, $I_{SD} = 9\text{ A}$, $V_{GS} = 0\text{ V}$, $R_{GS(on)} = 2.3\text{ }\Omega$, Q_{fr} includes also Q_C	$T_{vj} = 25\text{ °C}$		0.1		μC
			$T_{vj} = 175\text{ °C}$		0.18		
MOSFET peak forward recovery current	I_{frm}	$V_{DD} = 800\text{ V}$, $I_{SD} = 9\text{ A}$, $V_{GS} = 0\text{ V}$, $R_{GS(on)} = 2.3\text{ }\Omega$, Q_{fr} includes also Q_C	$T_{vj} = 25\text{ °C}$		19.9		A
			$T_{vj} = 175\text{ °C}$		32.5		
MOSFET forward recovery energy	E_{fr}	$V_{DD} = 800\text{ V}$, $I_{SD} = 9\text{ A}$, $V_{GS} = 0\text{ V}$, $R_{GS(on)} = 2.3\text{ }\Omega$, Q_{fr} includes also Q_C	$T_{vj} = 25\text{ °C}$		31		μJ
			$T_{vj} = 175\text{ °C}$		89		
MOSFET forward recovery energy at -5 V	E_{fr}	$V_{DD} = 800\text{ V}$, $I_{SD} = 9\text{ A}$, $V_{GS} = -5\text{ V}$, $R_{GS(on)} = 2.3\text{ }\Omega$, Q_{fr} includes also Q_C	$T_{vj} = 25\text{ °C}$		31		μJ
			$T_{vj} = 175\text{ °C}$		105		
Virtual junction temperature	T_{vj}			-55		175	$^{\circ}\text{C}$
Virtual junction temperature	$T_{vj(over)}$	overload, cumulative max. 100 h ¹⁾				200	$^{\circ}\text{C}$

1) 最多 5000 次循环。最大 ΔT 限制为 100 K。

4 特性图

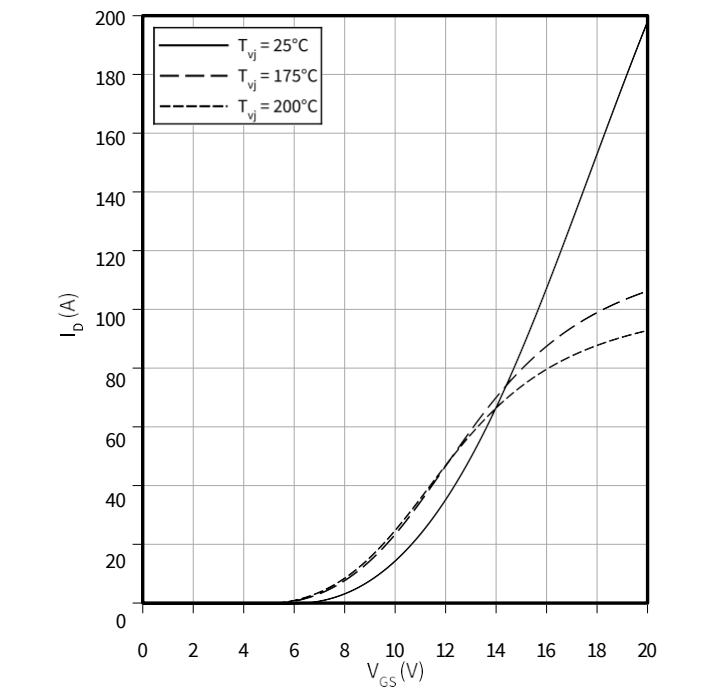
4 特性图



4 特性图

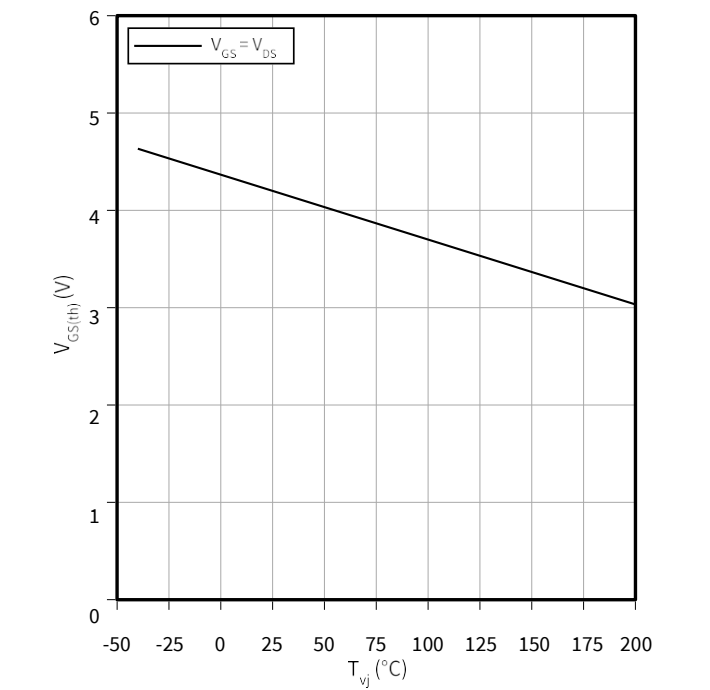
Typical transfer characteristic

$I_D = f(V_{GS})$
 $V_{DS} = 20\text{ V}$, $t_p = 20\text{ }\mu\text{s}$



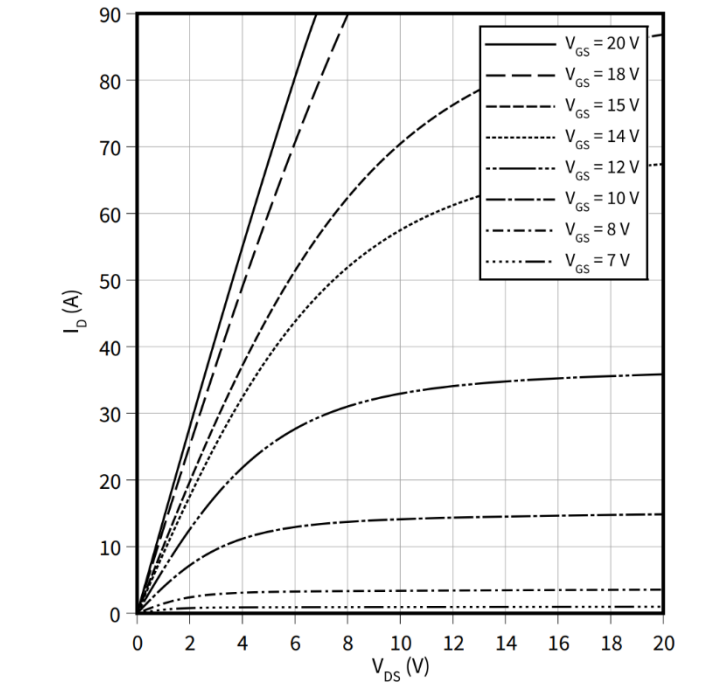
Typical gate-source threshold voltage as a function of junction temperature

$V_{GS(th)} = f(T_{vj})$
 $I_D = 2.8\text{ mA}$



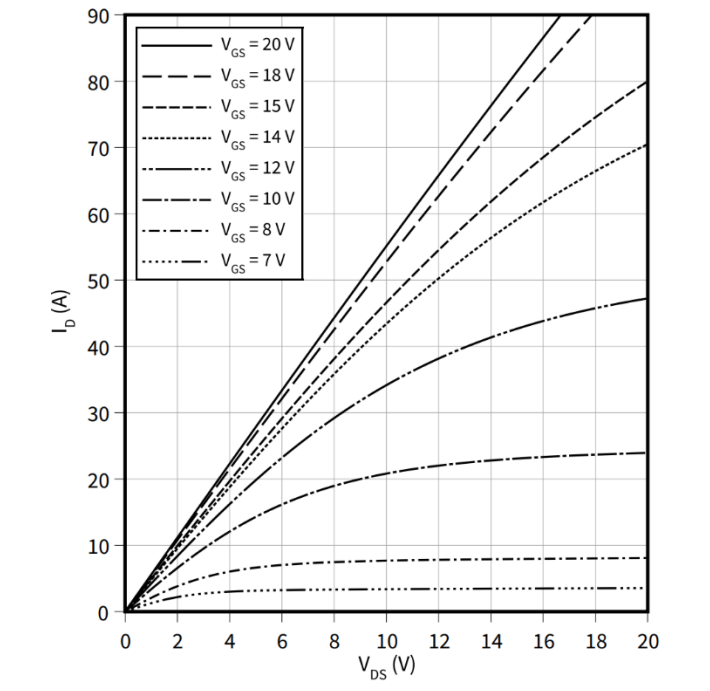
Typical output characteristic, V_{GS} as a parameter

$I_D = f(V_{DS})$
 $T_{vj} = 25\text{ }^\circ\text{C}$, $t_p = 20\text{ }\mu\text{s}$



Typical output characteristic, V_{GS} as a parameter

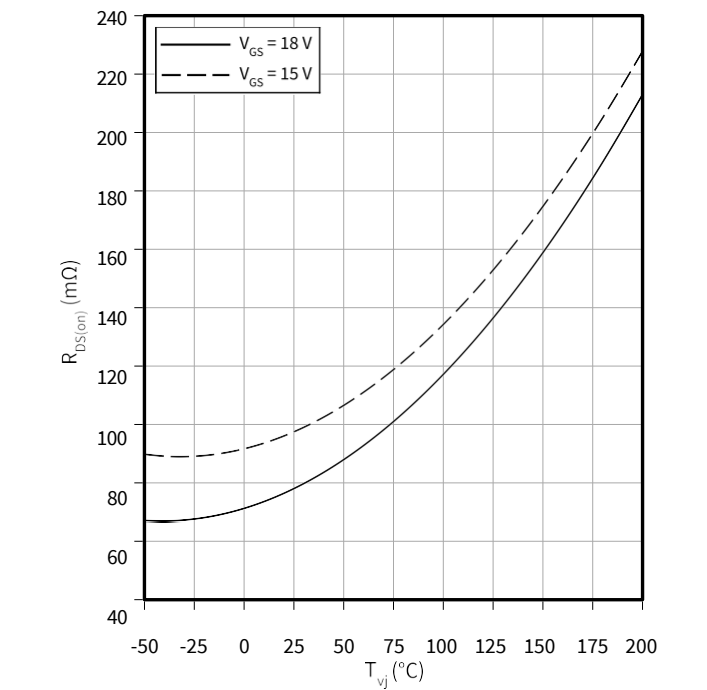
$I_D = f(V_{DS})$
 $T_{vj} = 175\text{ }^\circ\text{C}$, $t_p = 20\text{ }\mu\text{s}$



4 特性图

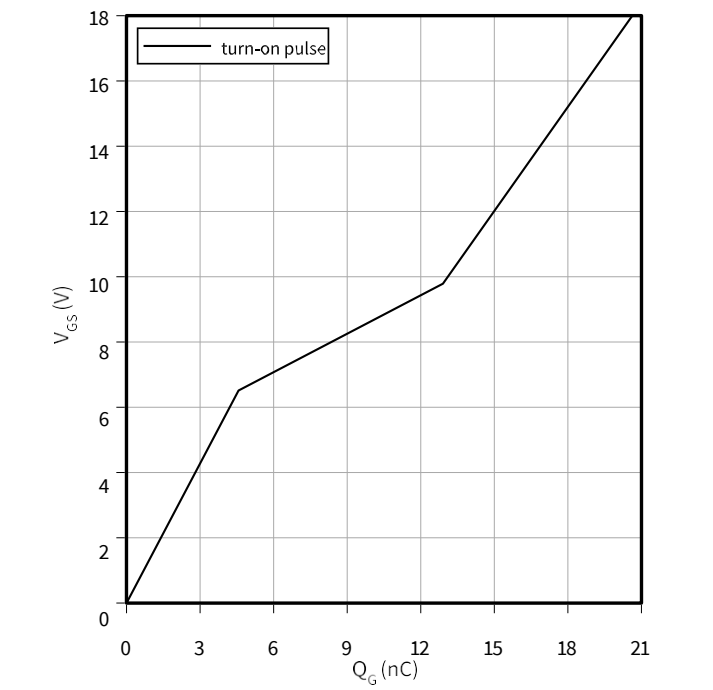
Typical on-state resistance as a function of junction temperature

$R_{DS(on)} = f(T_{vj})$
 $I_D = 9\text{ A}$



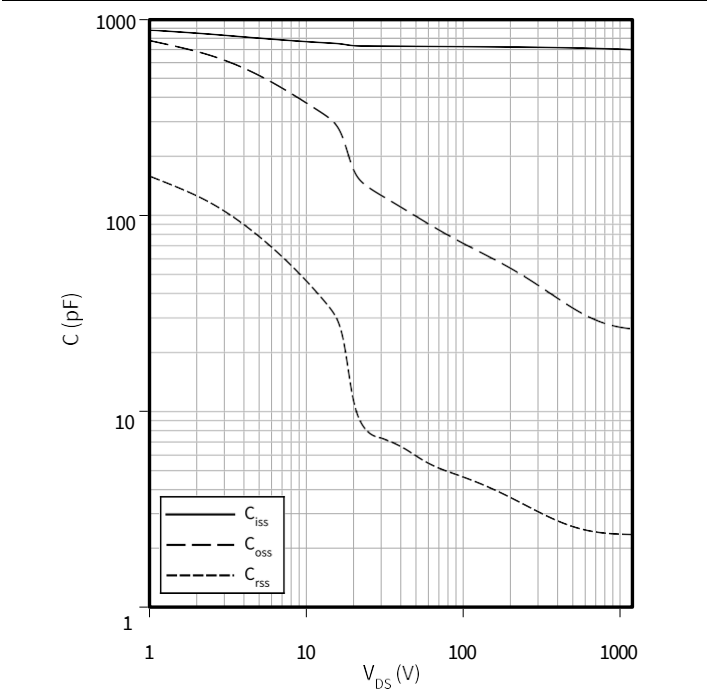
Typical gate charge

$V_{GS} = f(Q_G)$
 $I_D = 9\text{ A}, V_{DS} = 800\text{ V}$



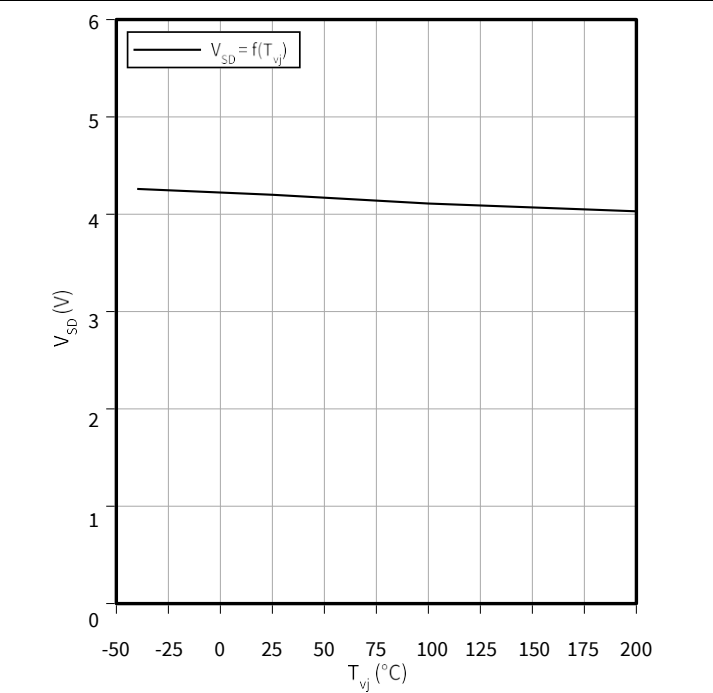
Typical capacitance as a function of drain-source voltage

$C = f(V_{DS})$
 $V_{GS} = 0\text{ V}, f = 100\text{ kHz}$



Typical reverse drain voltage as a function of junction temperature

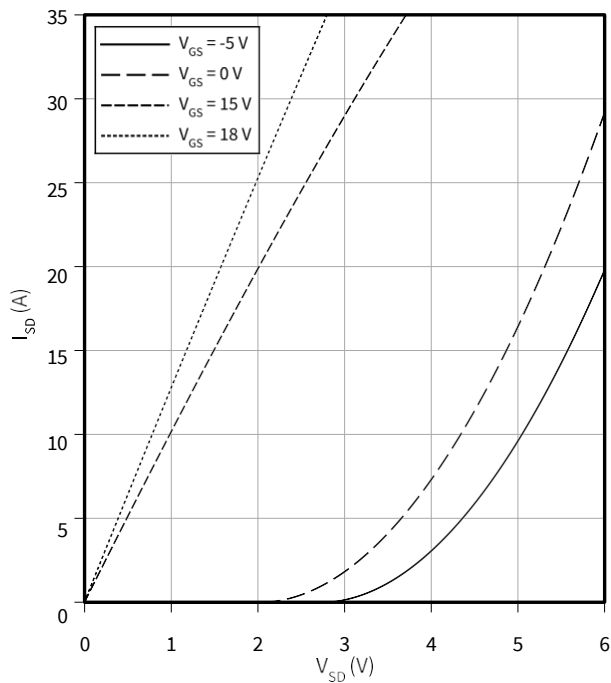
$V_{SD} = f(T_{vj})$
 $I_{SD} = 9\text{ A}, V_{GS} = 0\text{ V}$



4 特性图

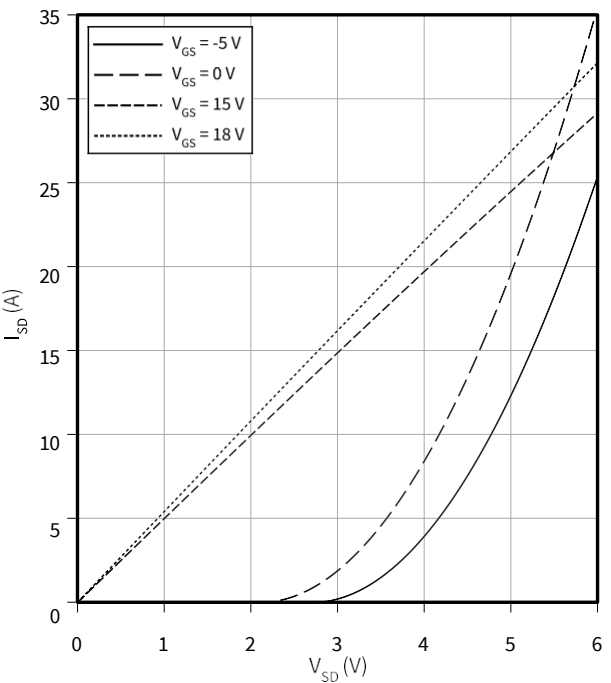
Typical reverse drain current as a function of reverse drain voltage, V_{GS} as a parameter

$I_{SD} = f(V_{SD})$
 $T_{vj} = 25\text{ }^{\circ}\text{C}$, $t_p = 20\text{ }\mu\text{s}$



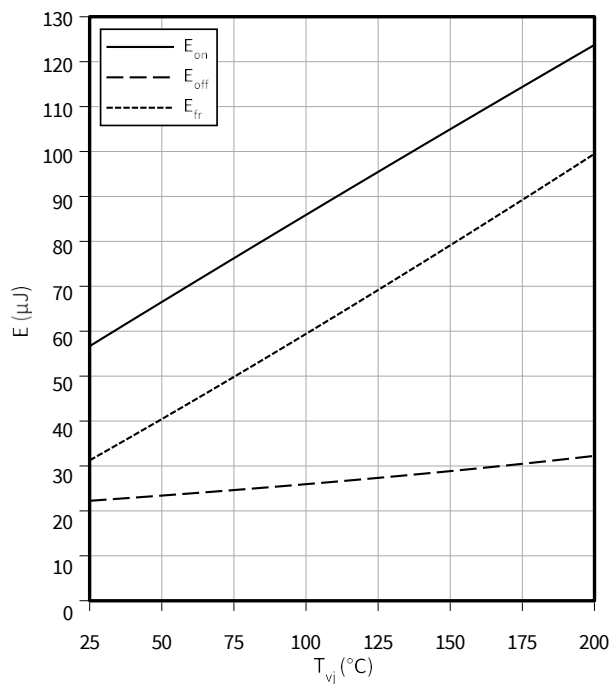
Typical reverse drain current as a function of reverse drain voltage, V_{GS} as a parameter

$I_{SD} = f(V_{SD})$
 $T_{vj} = 175\text{ }^{\circ}\text{C}$, $t_p = 20\text{ }\mu\text{s}$



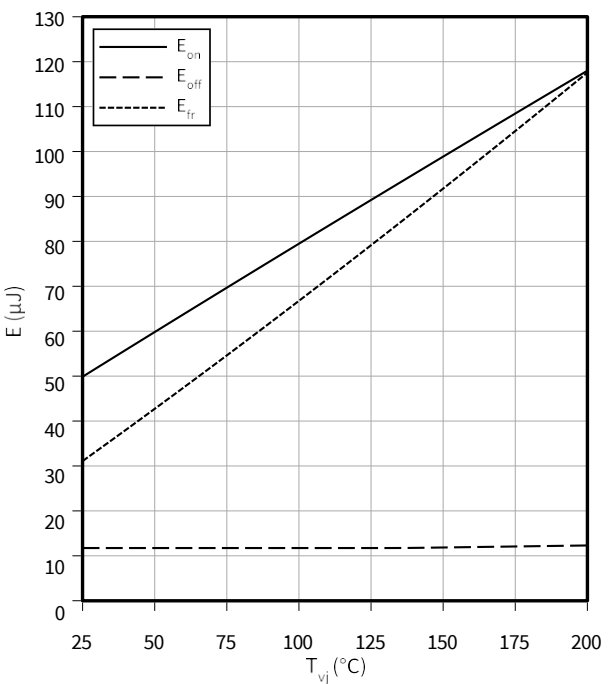
Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$E = f(T_{vj})$
 $V_{GS} = 0/18\text{ V}$, $I_D = 9\text{ A}$, $R_{G,ext} = 2.3\text{ }\Omega$, $V_{DD} = 800\text{ V}$



Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5\text{ V}$

$E = f(T_{vj})$
 $V_{GS} = -5/18\text{ V}$, $I_D = 9\text{ A}$, $R_{G,ext} = 2.3\text{ }\Omega$, $V_{DD} = 800\text{ V}$

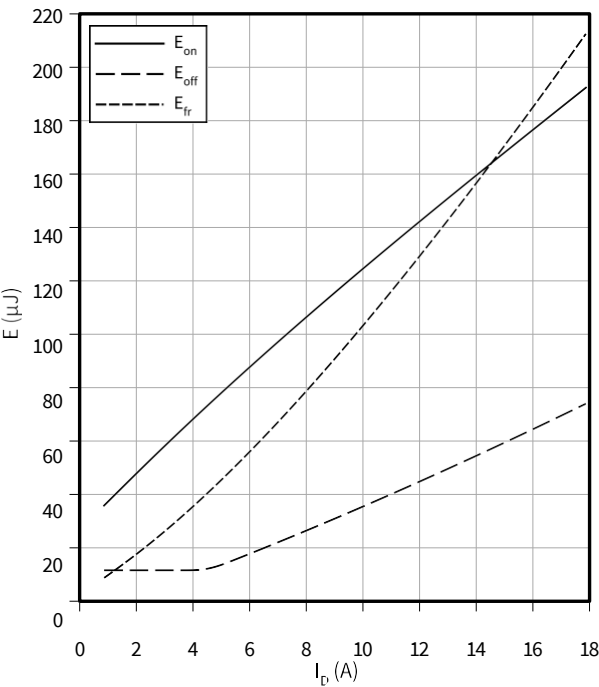


4 特性图

Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$E = f(I_D)$

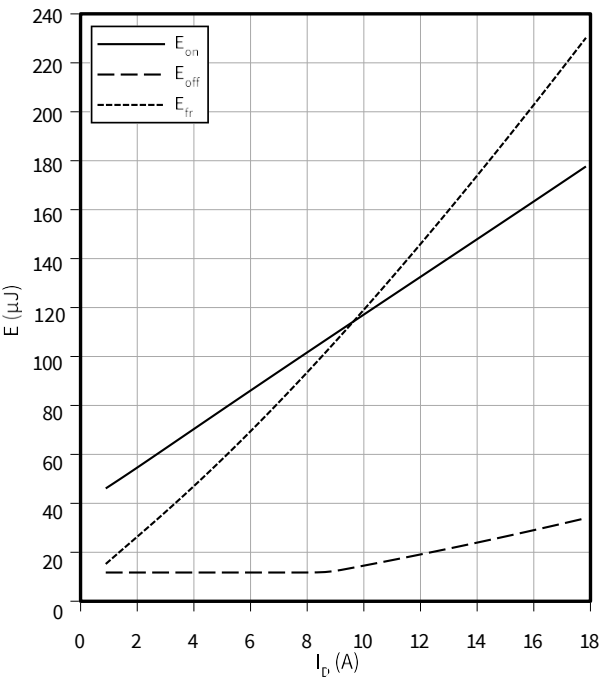
$V_{GS} = 0/18\text{ V}$, $T_{vj} = 175\text{ °C}$, $R_{G,ext} = 2.3\text{ }\Omega$, $V_{DD} = 800\text{ V}$



Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5\text{ V}$

$E = f(I_D)$

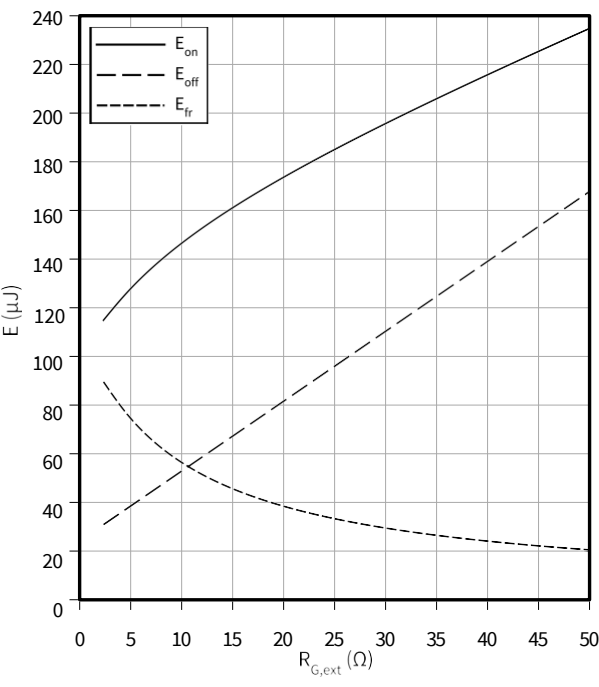
$V_{GS} = -5/18\text{ V}$, $T_{vj} = 175\text{ °C}$, $R_{G,ext} = 2.3\text{ }\Omega$, $V_{DD} = 800\text{ V}$



Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$E = f(R_{G,ext})$

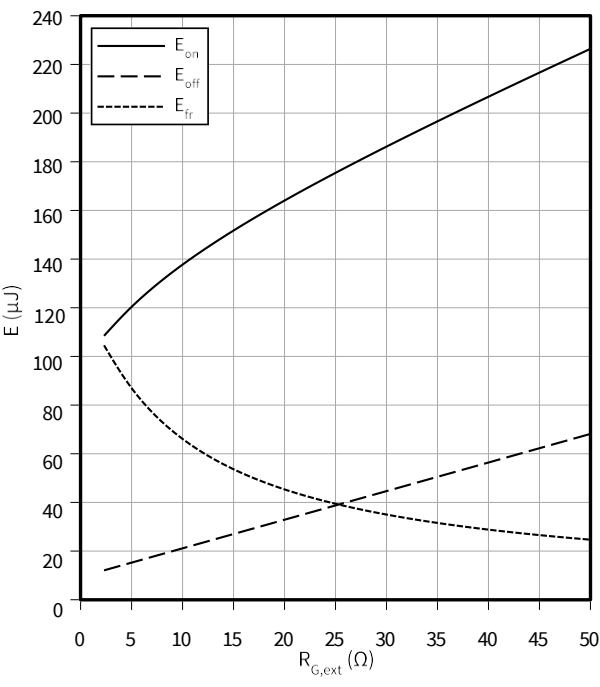
$V_{GS} = 0/18\text{ V}$, $I_D = 9\text{ A}$, $T_{vj} = 175\text{ °C}$, $V_{DD} = 800\text{ V}$



Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5\text{ V}$

$E = f(R_{G,ext})$

$V_{GS} = -5/18\text{ V}$, $I_D = 9\text{ A}$, $T_{vj} = 175\text{ °C}$, $V_{DD} = 800\text{ V}$

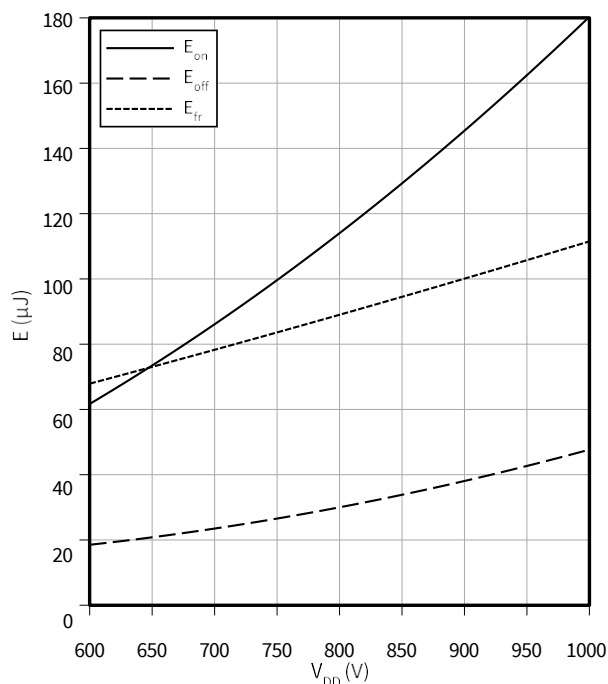


4 特性图

Typical switching energy as a function of DC link voltage, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$E = f(V_{DD})$$

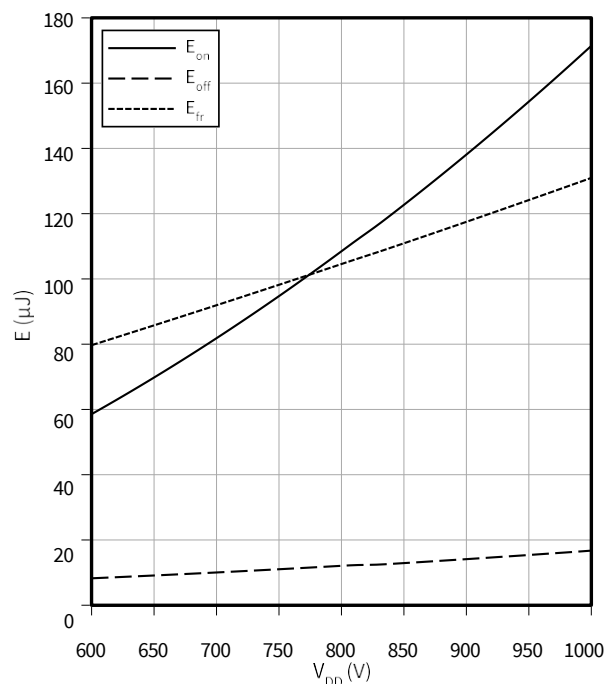
$V_{GS} = 0/18$ V, $I_D = 9$ A, $T_{vj} = 175$ °C, $R_{G,ext} = 2.3$ Ω



Typical switching energy as a function of DC link voltage, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = -5$ V

$$E = f(V_{DD})$$

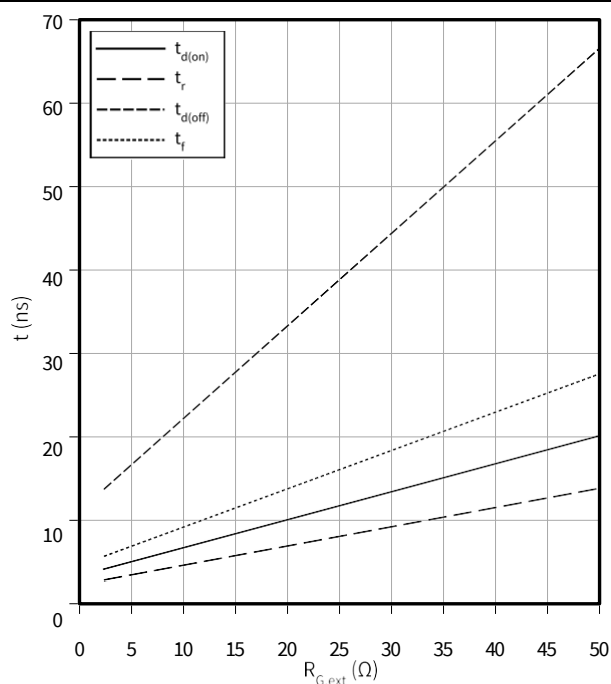
$V_{GS} = -5/18$ V, $I_D = 9$ A, $T_{vj} = 175$ °C, $R_{G,ext} = 2.3$ Ω



Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$t = f(R_{G,ext})$$

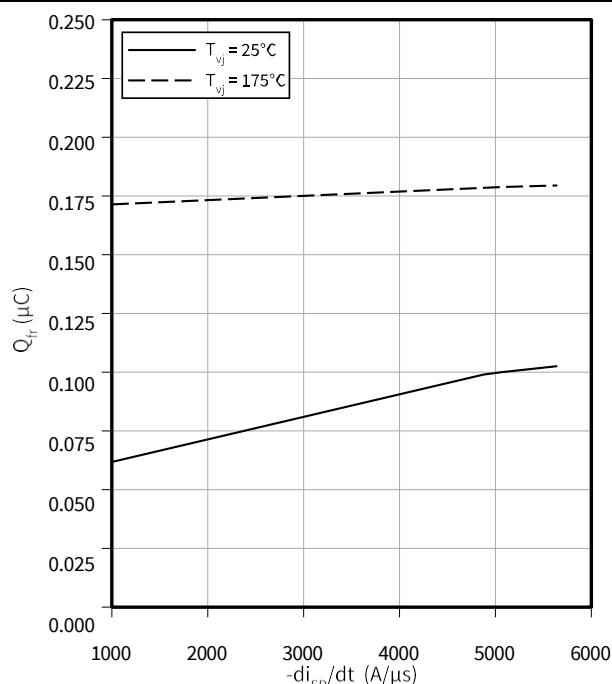
$V_{GS} = 0/18$ V, $I_D = 9$ A, $T_{vj} = 175$ °C, $V_{DD} = 800$ V



Typical reverse recovery charge as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$Q_{rr} = f(-di_{SD}/dt)$$

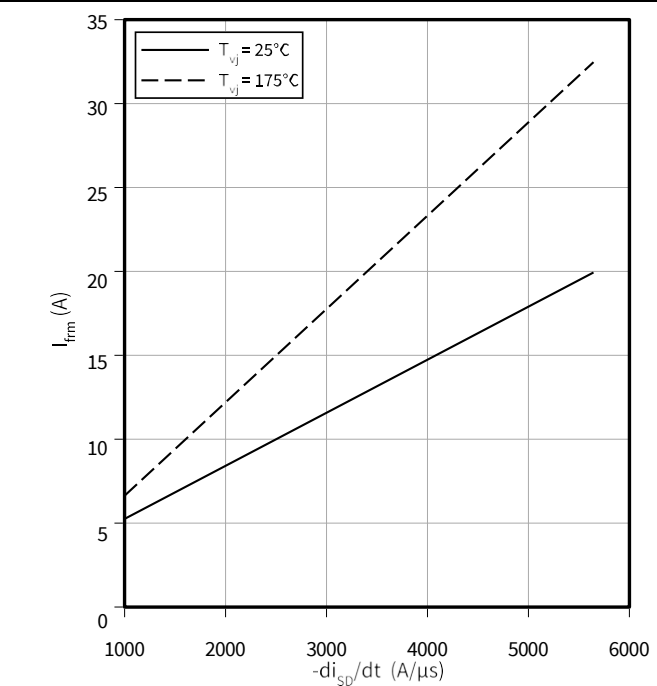
$V_{GS} = 0/18$ V, $I_{SD} = 9$ A, $V_{DD} = 800$ V



4 特性图

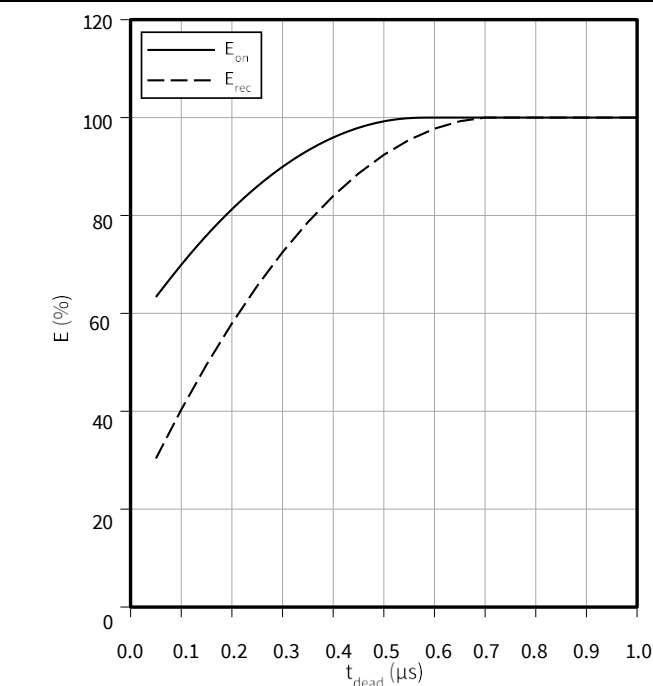
Typical reverse recovery current as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$I_{frm} = f(-di_{SD}/dt)$
 $V_{GS} = 0/18\text{ V}, I_{SD} = 9\text{ A}, V_{DD} = 800\text{ V}$



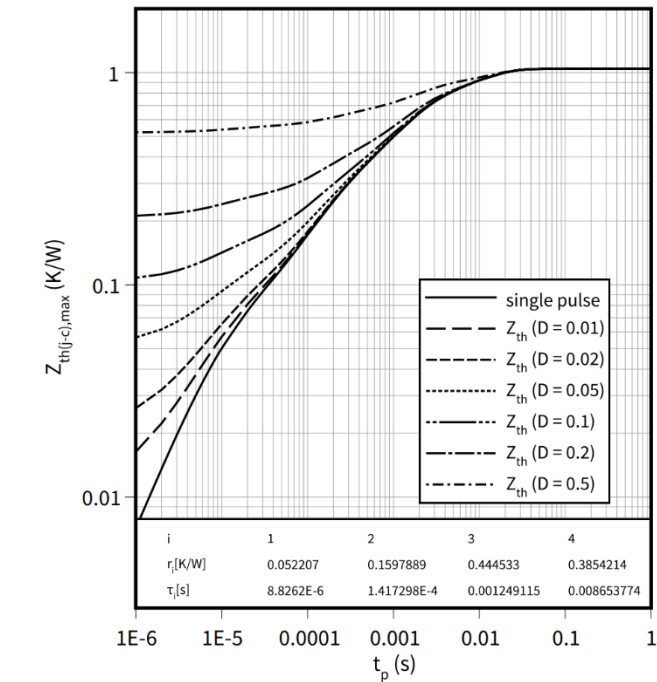
Typical switching energy as a function of dead time / blanking time, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$E = f(t_{dead})$
 $I_D = 9\text{ A}, V_{GS} = 0/18\text{ V}, T_{vj} = 175\text{ °C}, R_{G,ext} = 2.3\text{ }\Omega, V_{DD} = 800\text{ V}$



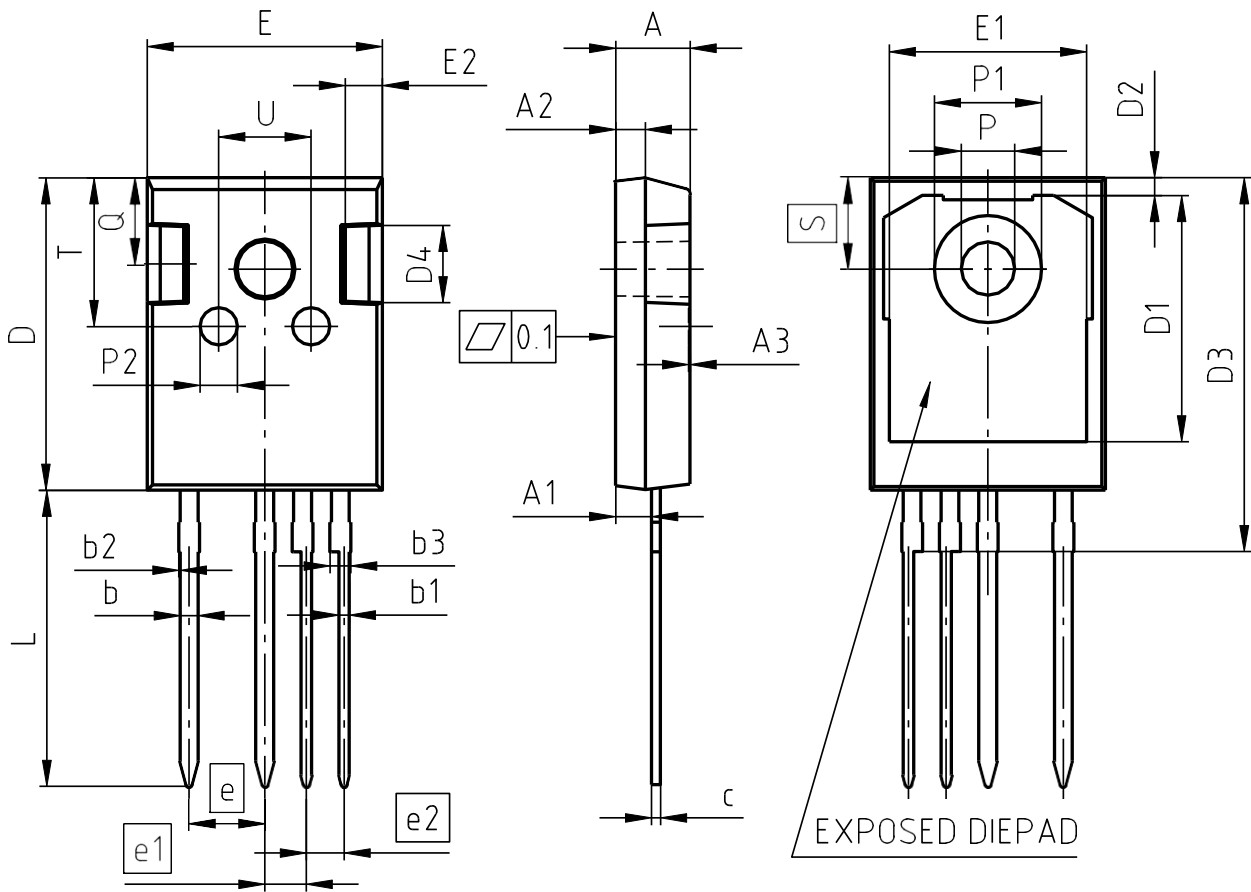
Max. transient thermal impedance (MOSFET/diode)

$Z_{th(j-c),max} = f(t_p)$
 $D = t_p/T$



5 封装外形

5 封装外形



NOTES:
ALL DIMENSIONS DO NOT INCLUDE MOLD FLASH
OR PROTRUSIONS.

PACKAGE - GROUP PG-TO247-4-U02					
NUMBER:					
DIMENSIONS	MILLIMETERS		DIMENSIONS	MILLIMETERS	
	MIN.	MAX.		MIN.	MAX.
A	4.90	5.10	E	15.70	15.90
A1	2.31	2.51	E1	13.10	13.50
A2	1.90	2.10	E2	2.40	2.60
A3	0.05	0.25	e	5.08	
b	1.10	1.30	e1	2.79	
b1	0.65	0.79	e2	2.54	
b2	---	0.20	N	4	
b3	1.34	1.44	L	19.80	20.10
c	0.58	0.66	øP	3.50	3.70
D	20.90	21.10	øP1	7.00	7.40
D1	16.25	16.85	øP2	2.40	2.60
D2	1.05	1.35	Q	5.60	6.00
D3	24.97	25.27	S	6.15	
D4	4.90	5.10	T	9.80	10.20
			U	6.00	6.40

图 1

6 测试条件

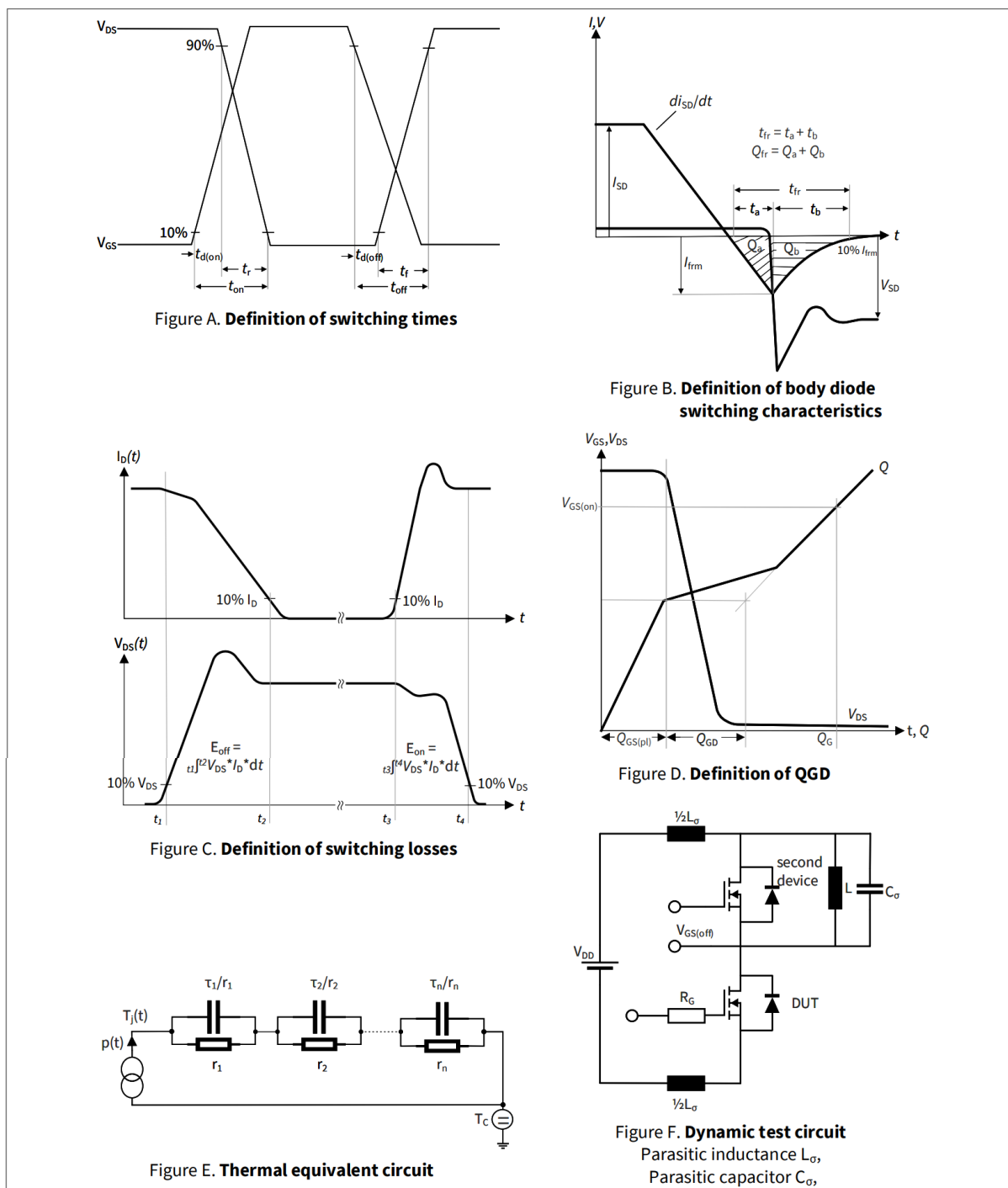


图 2



修订记录

修订记录

Document revision	Date of release	Description of changes
0.10	2025-03-24	Preliminary datasheet
1.00	2025-03-25	Final datasheet
1.10	2025-07-04	Increased I_{DM} in Table 2 Added switching information for $V_{GS} = -5/18\text{ V}$ in Table 5 and 6 and corresponding diagrams Added I_{SDC} in Table 5 Added SOA diagram on page 8 Added diagram $E = f(V_{DD}) @ V_{GS} = 0/18\text{ V}$ Added diagram $E = f(V_{DD}) @ V_{GS} = -5/18\text{ V}$ Editorial changes



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